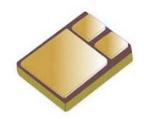


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Features

- JAN, JANTX, JANTXV, JANS and JANSR Qualified to MIL-PRF-19500/560
- Radiation Tolerant Levels M, D, P, L and R
- Lightweight & Low Power
- Ideal for Space, Military and Other High Reliability Applications
- Surface Mount U3 Package



Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.		
		T	T				
Collector - Emitter Breakdown Voltage	I _C = 50 mA dc	$V_{(BR)CEO}$	V dc	100	_		
Collector - Emitter Cutoff Current	$V_{CE} = 100 \text{ V dc}$ $V_{CE} = 90 \text{ V dc}, V_{BE} = 1.5 \text{ V dc}$	I _{CEO}	μA dc	_	100 1.0		
Collector - Base Cutoff Current	V _{CB} = 100 Vdc	I _{CBO}	μA dc	_	1.0		
Emitter - Base Cutoff Current	V _{EB} = 6.0 Vdc	I _{EBO}	μA dc	_	100		
		T	T				
Forward Current Transfer Ratio	I_{C} = 0.5 A dc, V_{CE} = 2.0 V dc I_{C} = 2.0 A dc, V_{CE} = 2.0 V dc I_{C} = 5.0 A dc, V_{CE} = 2.0 V dc	h _{FE}	-	60 60 40	240		
Collector - Emitter Saturation Voltage	$I_C = 2.0 \text{ A dc}, I_B = 0.2 \text{ A dc}$ $I_C = 5.0 \text{ A dc}, I_B = 0.5 \text{ A dc}$	V _{CE(SAT)1} V _{CE(SAT)2}	V dc	_	0.7 1.2		
Emitter - Base Saturation Voltage	$I_C = 2.0 \text{ A dc}, I_B = 0.2 \text{ A dc}$ $I_C = 5.0 \text{ A dc}, I_B = 0.5 \text{ A dc}$	V _{BE(SAT)1}	V dc	_	1.2 1.8		
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}C$ $V_{CE} = 90 \text{ V dc}, V_{BE} = 1.5 \text{ V dc}$	I _{CEX2}	mA dc	_	1.0		
Forward - Current Transfer Ratio	$V_{CE} = 2.0 \text{ V dc}, I_{C} = 2.0 \text{ A dc}$	h _{FE4}	-	12			
Dynamic Characteristics							
Small-Signal Short-Circuit Forward Current Transfer Ratio	I _C = 0.5 A dc, V _{CE} = 10 V dc, f = 10 MHz	h _{fe}	-	3	15		
Output Capacitance	V _{CB} = 10 V dc, I _E = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	250		
Input Capacitance	$V_{BE} = 2 \text{ V dc}, I_{C} = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$	C _{ibo}	pF	_	1000		



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Absolute Maximum Ratings (T_A = +25°C unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	V _{CEO}	100 V dc
Collector - Base Voltage	V _{CBO}	100 V dc
Emitter - Base Voltage	V _{EBO}	6 V dc
Base Current	I _B	1 A dc
Collector Current	Ic	5 A dc
Total Power Dissipation ⁽¹⁾ @ T _A = 25°C @ T _C = 25°C	P _T	1.0 W 75 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

^{1.} For derating, see figures 6, 7, and 8 of MIL-PRF-19500/560.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	R _{0JC}	2.3°C/W

Parameter	Test Conditions	Symbol	Units	Min.	Max.	
Pulse Response						
Pulse Delay Time	See Figure 12 of MIL-PRF-19500/560	t _d	ns	_	100	
Pulse Rise Time	See Figure 12 of MIL-PRF-19500/560	t _r	ns	_	100	
Pulse Storage Time	See Figure 13 of MIL-PRF-19500/560	ts	μs	_	2	
Pulse Fall Time	See Figure 13 of MIL-PRF-19500/560	t _f	ns	_	200	

Safe Operating Area

DC Tests: $T_C = +25^{\circ}C$, I Cycle, $t \ge 0.5$ s

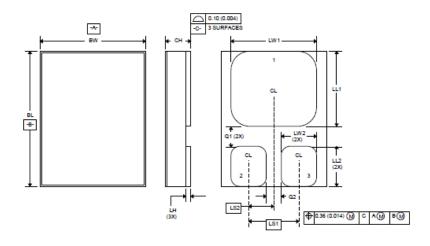
Test 1: $V_{CE} = 2 \text{ Vdc}, I_{C} = 5 \text{ A dc}$ Test 2: $V_{CE} = 5 \text{ Vdc}, I_{C} = 2 \text{ A dc}$ Test 3: $V_{CE} = 90 \text{ Vdc}, I_{C} = 55 \text{ mA dc}$

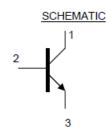


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Outline Drawing (U3)





Ltr	Dimensions				
	Inches		Millimeters		
	Min	Max	Min	Max	
BL	.395	.405	10.03	10.29	
BW	.291	.301	7.40	7.65	
CH	.1085	.1205	2.76	3.06	
LH	.010	.020	0.25	0.51	
LW1	.281	.291	7.14	7.39	
LW2	.090	.100	2.29	2.54	
LL1	.220	.230	5.59	5.84	
LL2	.115	.125	2.92	3.18	
LS1	.150 BSC		3.81 BSC		
LS2	.075 BSC		1.91 BSC		
Q1	.030		0.762		
Q2	.030		0.762		

NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
- 3. Terminal 1 collector, terminal 2 -base, terminal 3 emitter.

FIGURE 2. Physical dimensions and configuration (U3) (SMD 5) (TO-276AA).

2N5339U3



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